



2SK4067 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Motor drive applications.
- 4.5V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		30	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		8	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	32	A
Allowable Power Dissipation	P _D		1	W
		T _c =25°C	10	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0V	30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.5		2.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =4A	2.6	4.4		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =8A, V _{GS} =10V		85	115	mΩ
	R _{DS(on)2}	I _D =4A, V _{GS} =4.5V		155	220	mΩ
Input Capacitance	C _{iss}	V _{DS} =10V, f=1MHz		260		pF
Output Capacitance	C _{oss}	V _{DS} =10V, f=1MHz		65		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =10V, f=1MHz		40		pF

Marking : K4067

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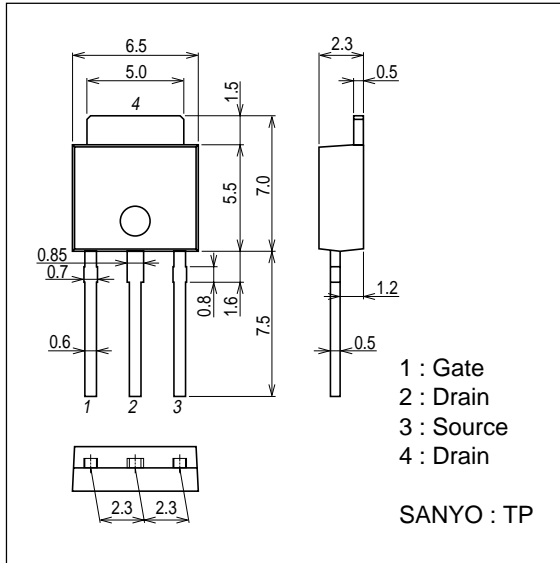
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_d(\text{on})$	See specified Test Circuit.		9		ns
Rise Time	t_r	See specified Test Circuit.		8		ns
Turn-OFF Delay Time	$t_d(\text{off})$	See specified Test Circuit.		19		ns
Fall Time	t_f	See specified Test Circuit.		8		ns
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=10V, I_D=8A$		6		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=10V, V_{GS}=10V, I_D=8A$		1.2		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=10V, V_{GS}=10V, I_D=8A$		1.0		nC
Diode Forward Voltage	V_{SD}	$I_S=8A, V_{GS}=0V$	1.05	1.2		V

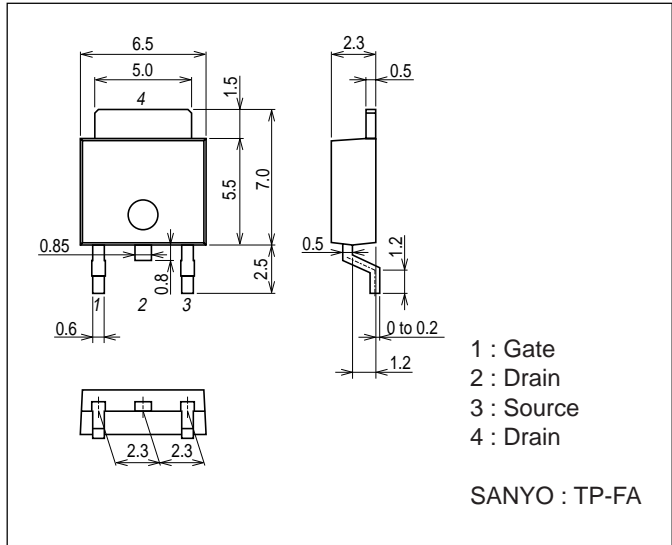
Package Dimensions

unit : mm (typ)
7518-004

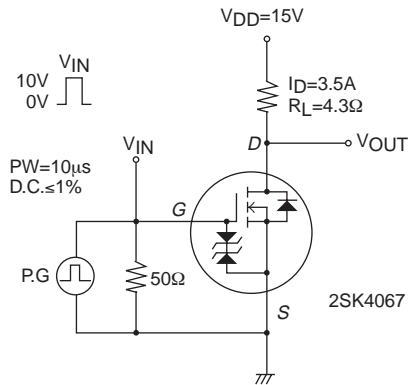


Package Dimensions

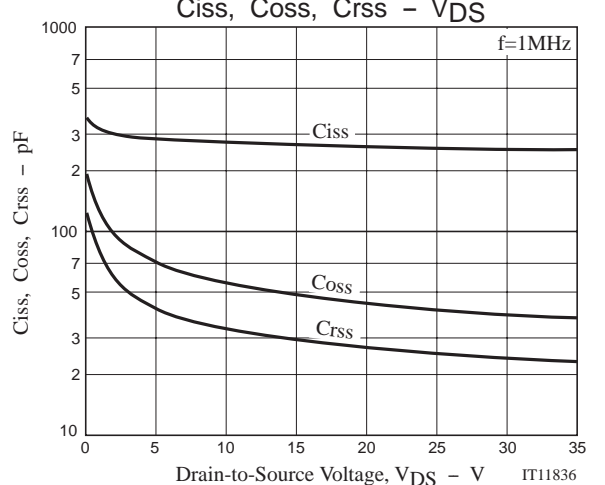
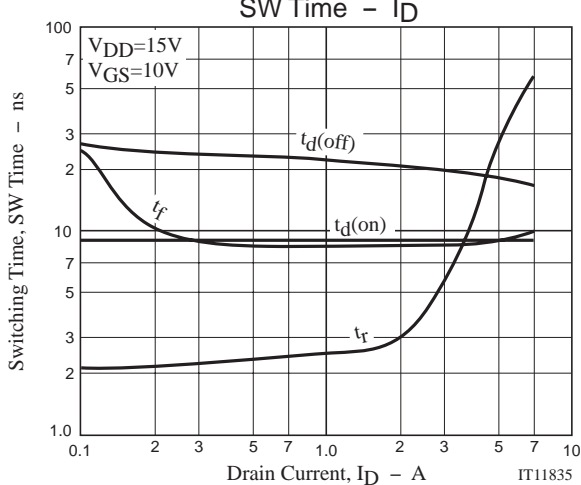
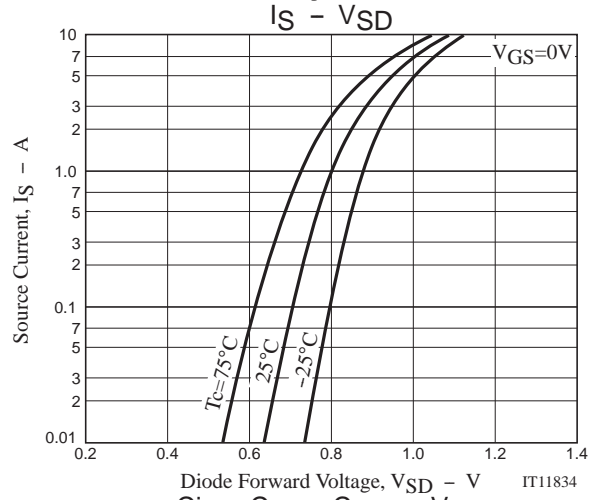
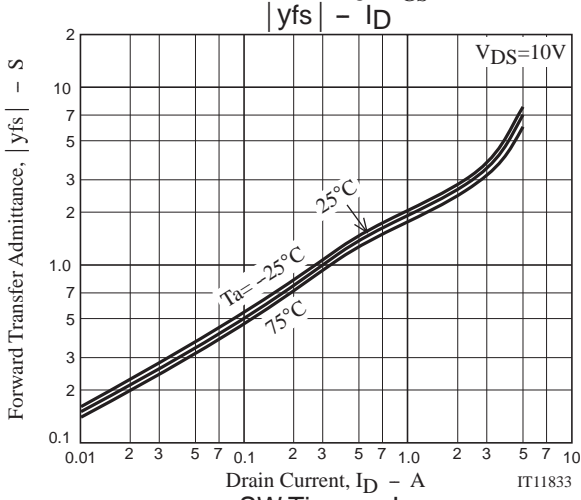
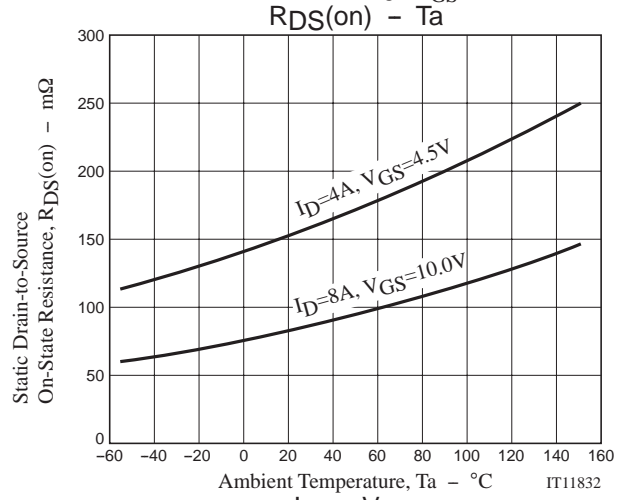
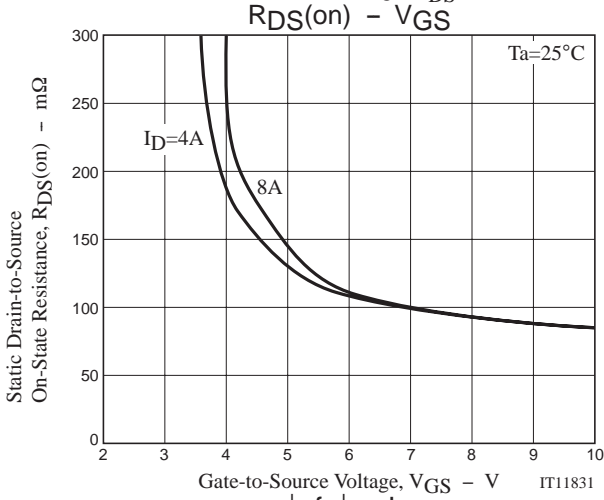
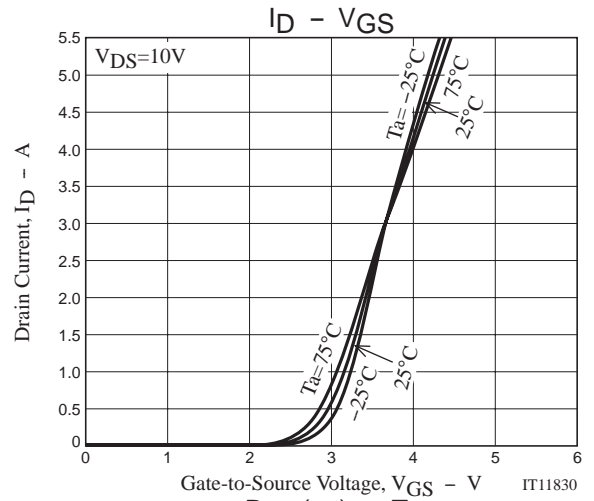
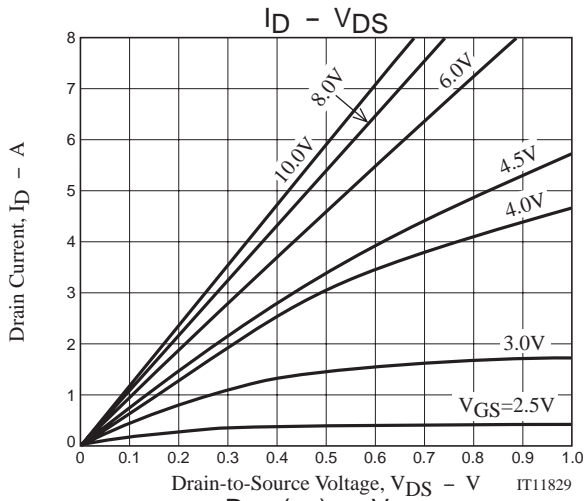
unit : mm (typ)
7003-004

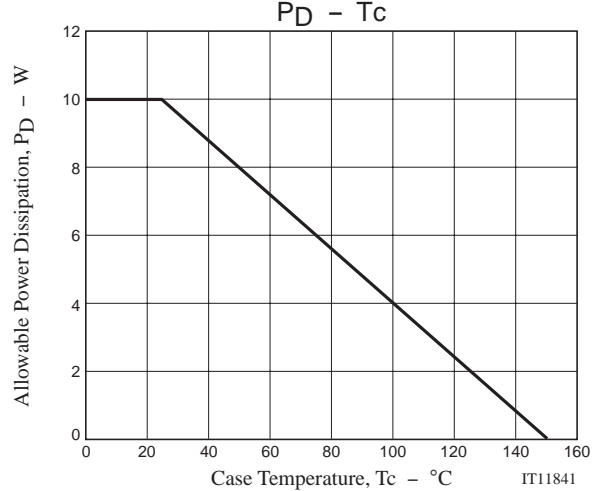
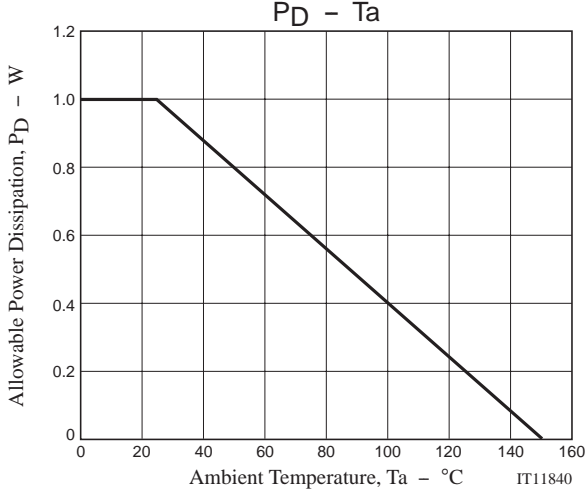
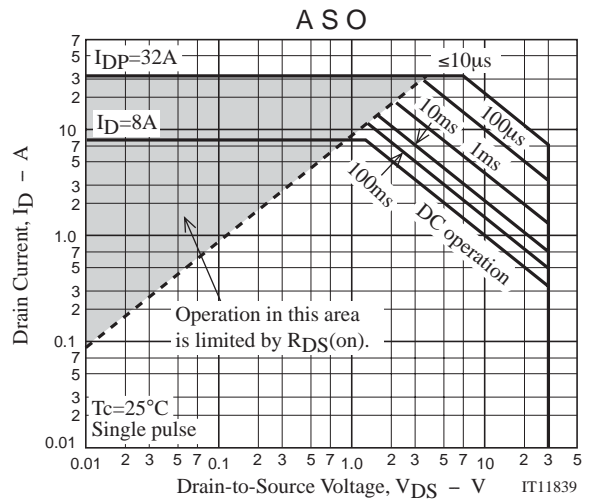
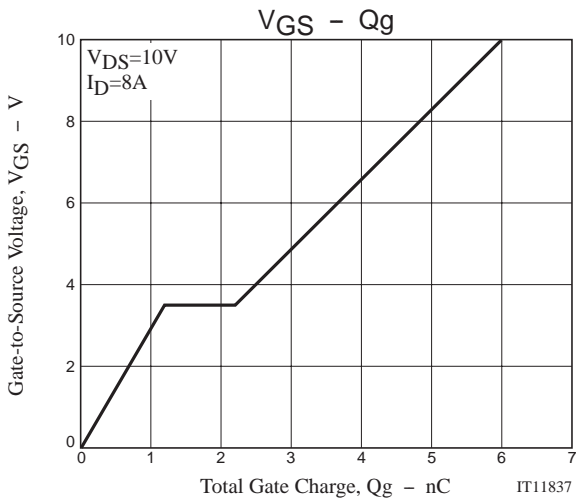


Switching Time Test Circuit



2SK4067





Note on usage : Since the 2SK4067 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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